

30 V, Dual N-channel Trench MOSFET 15 April 2016

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							,
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	0.95	А
Static characteristics (per transistor)							
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 0.9 A; T _j = 25 °C		-	211	252	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2		$G1 \xrightarrow{f} G2$
4	S2	source TR2		
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PMGD175XNE	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

7. Marking

Table 4. Marking codes	
Type number	Marking code
	[1]
PMGD175XNE	LU%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5.Limiting values

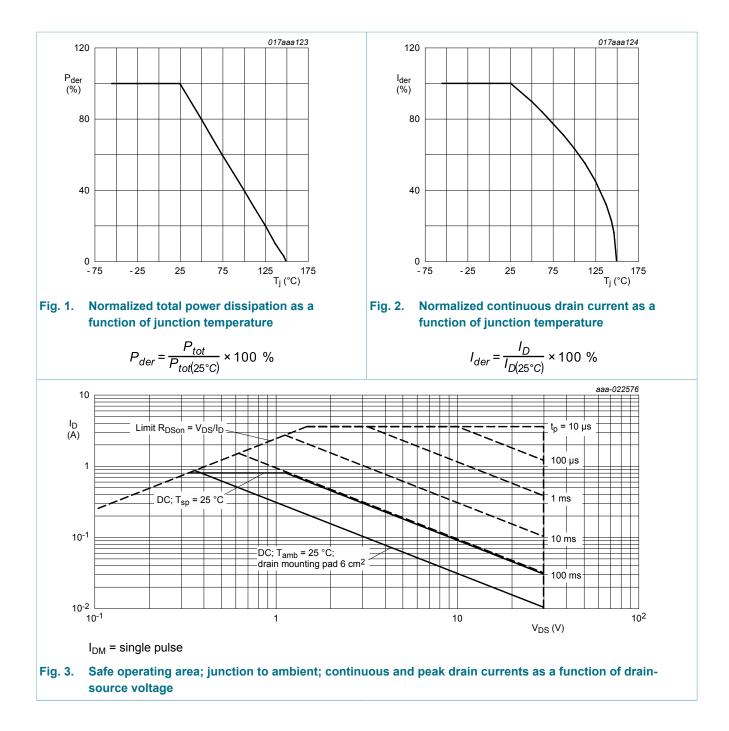
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
Per transis	tor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	0.95	А
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	0.87	А
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.5	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	4	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	260	m₩
			[1]	-	310	mΨ
		T _{sp} = 25 °C		-	905	mW
Per device				·	·	
P _{tot}	total power dissipation	T _{amb} = 25 °C	<u>[2]</u>	-	390	m₩
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode	· ·				
I _S	source current	T _{amb} = 25 °C	[1]	-	0.31	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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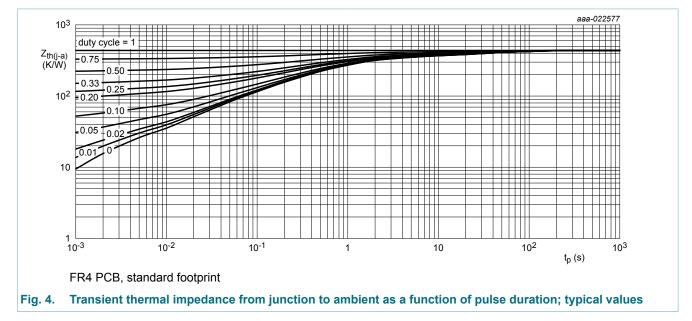
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Thermal characteristics 9.

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transistor	·						_
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance		[1]	-	417	480	K/W
	-		[2]	-	352	405	K/W
	ampient	in free air; t ≤ 5 s	[2]	-	295	340	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	120	138	K/W
Per device							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	320	K/W

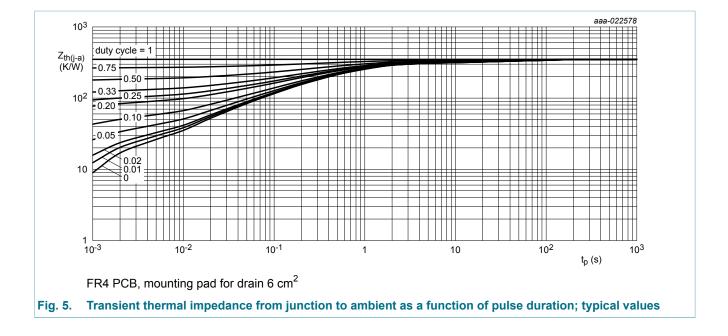
Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1] [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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10. Characteristics

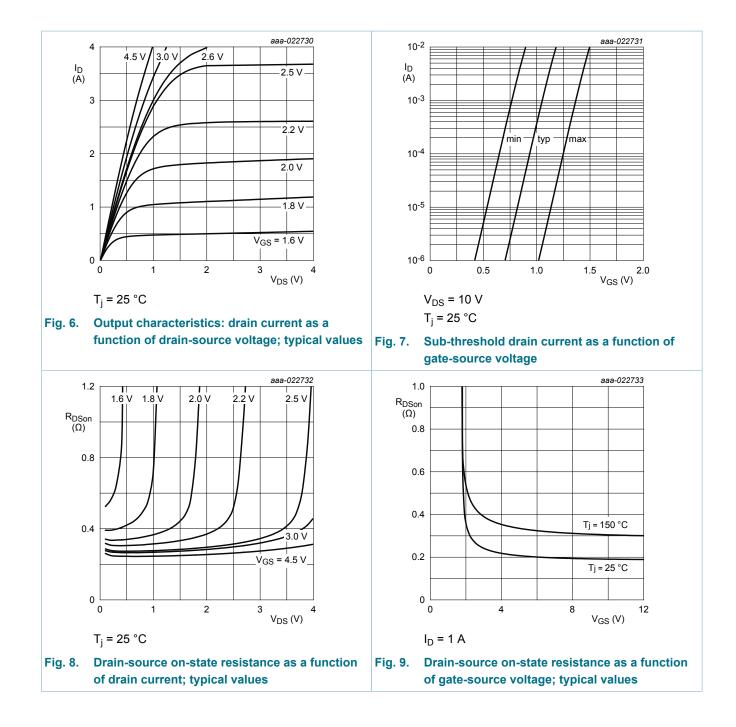
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)	L				
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = 25 °C	0.75	1	1.25	V
I _{DSS}	drain leakage current	V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	5	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I _D = 0.9 A; T _j = 25 °C	-	211	252	mΩ
resista		V _{GS} = 4.5 V; I _D = 0.9 A; T _j = 150 °C	-	344	411	mΩ
		V _{GS} = 2.5 V; I _D = 0.8 A; T _j = 25 °C	-	267	319	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I _D = 0.9 A; T _j = 25 °C	-	3.5	-	S
Dynamic ch	aracteristics (per transist	or)	I			
Q _{G(tot)}	total gate charge	V_{DS} = 15 V; I _D = 0.9 A; V _{GS} = 4.5 V;	-	1.05	1.65	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.15	-	nC
Q _{GD}	gate-drain charge		-	0.27	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	81	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	13	-	pF
C _{rss}	reverse transfer capacitance		-	9	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I _D = 0.9 A; V _{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	14	-	ns
t _{d(off)}	turn-off delay time	1	-	17	-	ns
t _f	fall time	1	-	6	-	ns
Source-drai	in diode (per transistor)	1	I			
V _{SD}	source-drain voltage	I _S = 0.3 A; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	V

PMGD175XNE

Product data sheet

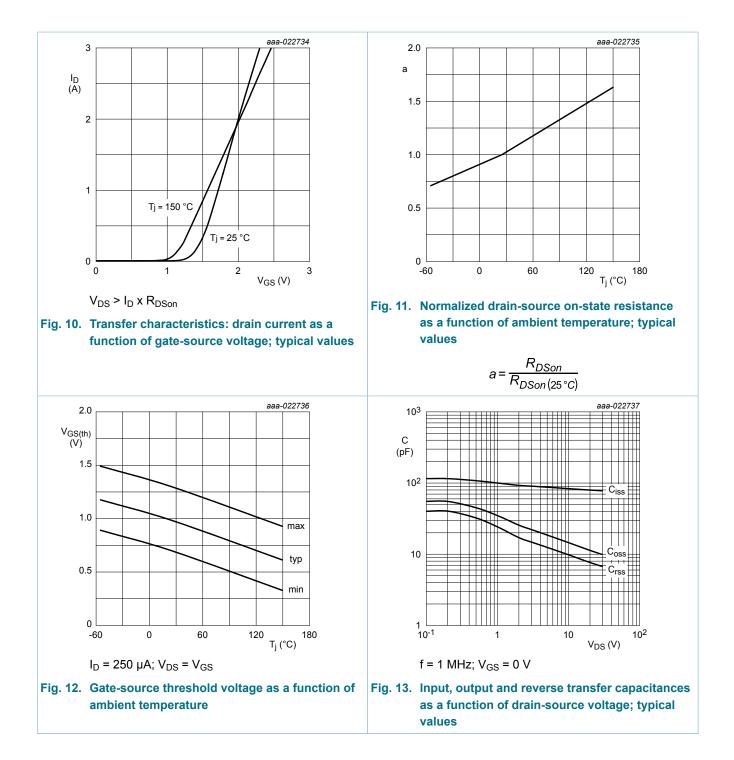
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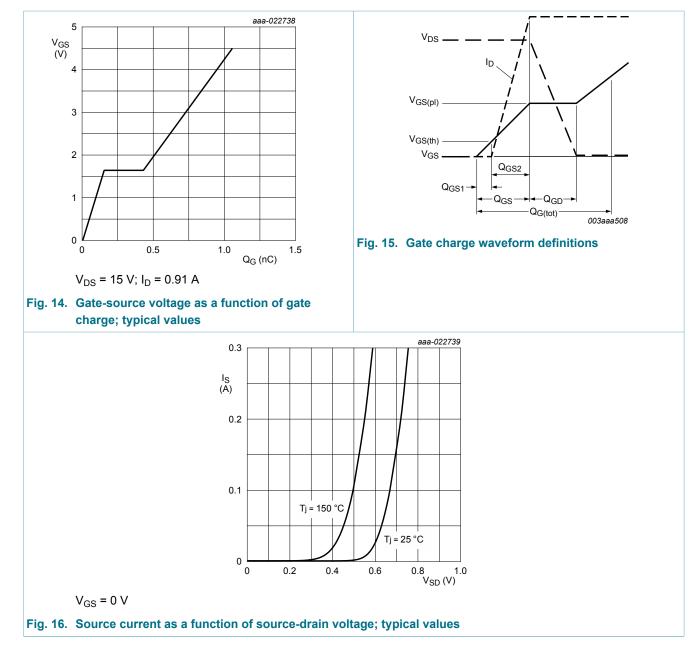
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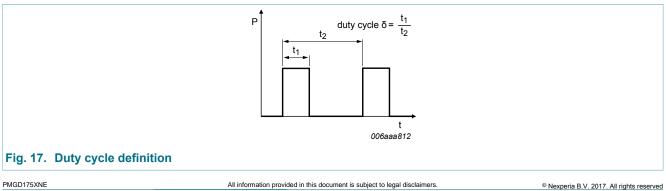
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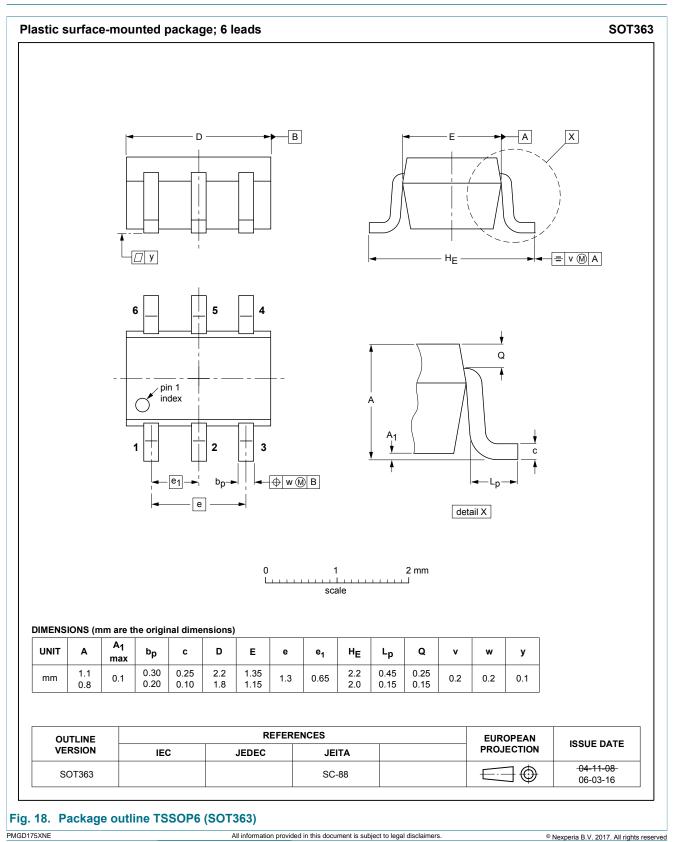


11. Test information



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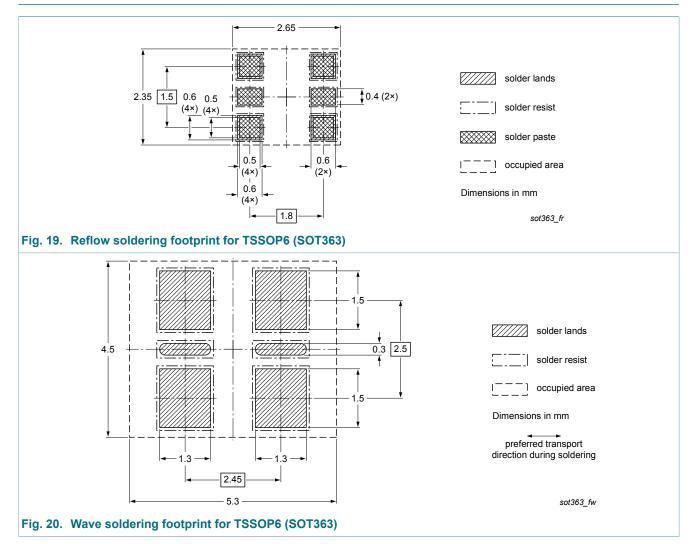
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision his	e 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMGD175XNE v.1	20160415	Product data sheet	-	-			

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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